

15Amp. MOS BARRIER RECTIFIER

SKM1550USP

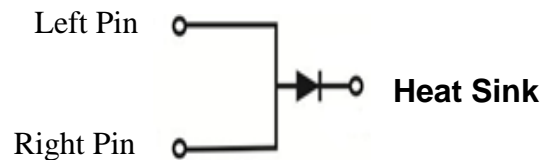
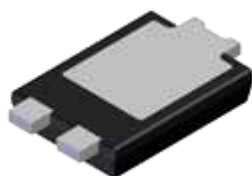
$I_{F(AV)}$	15A
V_{RRM}	50V
V_F at 125°C	0.43V
T_j	150°C

Features

- 150°C operating junction temperature
- Softest, fast switching capability
- Reduced ultra-low forward voltage drop (VF) ; better efficiency and cooler operation.
- Lead-Free Finish; RoHS Compliant
- Halogen and Antimony Free. “Green” Device
- MCD technology provides a superior avalanche capability than schottky diodes

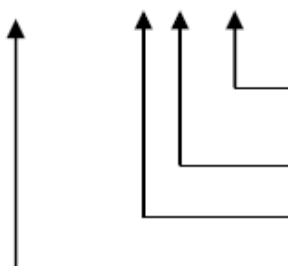
Mechanical Data

- Case: TO-277 molded plastic
- Mounting Position: Any
- Weight: 0.093 grams (approximate)
- Terminals: Pure tin plated, solderable per JESD22-B102
- Epoxy: UL 94V-0 rate flame retardant
- Polarity : As marked.



Ordering Information

Device	Package	Shipping
SKM1550USP-0-TD-G	TO-277 (RoHS compliant package)	5000/Tape & Reel



Environment friendly grade : S for RoHS compliant products, G for RoHS compliant and green compound products
 Packing spec, TD : 5000 pcs / tape & reel, 13" reel
 Product rank, zero for no rank products
 Product name

Marking Information



CYS= Manufacturers' Code Marking
 M1550U = Product Type Marking Code
 Y M = Date Code Marking
 Y = Last One Digits of Year (ex: 4 for 2014)
 M = Month Code (1 ~ 9、10→A、11→B、12→C)
 X= Assembly Site Code

Maximum Ratings and Electrical Characteristics

(Rating at 25°C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.)

Parameter	Symbol	Min.	Typ.	Max.	Units
Maximum DC blocking voltage	V _{DC}			50	V
Maximum Recurrent peak reverse voltage	V _{RRM}			50	V
Maximum RMS voltage	V _{RMS}			36	V
Maximum instantaneous forward voltage at I _F =15A	V _F	T _C =25°C	0.47	0.52	v
		T _C =125°C	0.43	0.47	
Maximum instantaneous reverse current at	I _R	V _R =50 V, T _C =25°C	110	500	μA
		V _R =50 V, T _C =125°C	40	100	mA
Maximum Average forward rectified current @ T _C =100°C	I _{F(AV)}			15	A
Non-repetitive peak forward surge current @ 8.3ms single half sine wave superimposed on rated load (JEDEC method)	I _{FSM}			280	A
Peak Repetitive Reverse Surge Current (2uS-1Khz)	I _{RRM}			2	A
Maximum Rate of Voltage Change (at Rated V _R)	dv/dt			10000	V/uS
Storage temperature range	T _{stg}	-55		150	°C
Operating junction temperature range	T _J	-55		150	°C

Thermal Data

Parameter	Symbol	Value	Unit
Maximum Thermal Resistance, Junction-to-ambient(1)	R _{th,j-a}	97	°C/W
Maximum Thermal Resistance, Junction-to-ambient(2)	R _{th,j-a}	39	°C/W

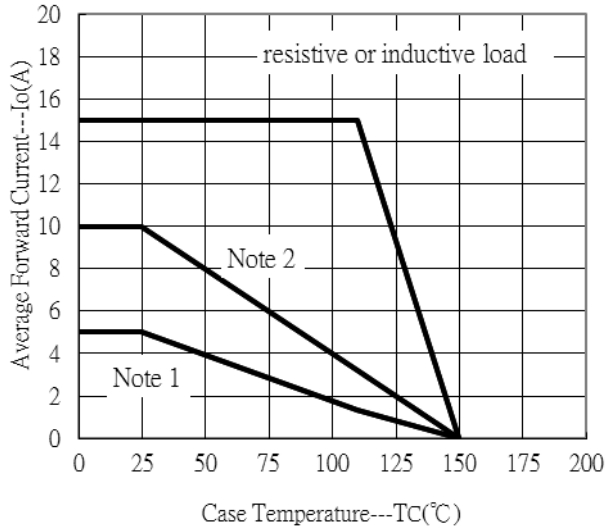
Note

1. FR-4 PCB, 2oz. Copper. Minimum recommended pad layout.

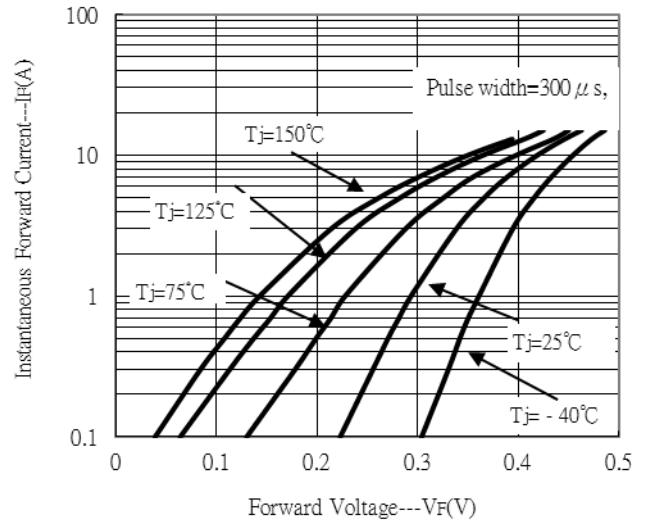
2. FR-4 PCB, 2oz. Copper. Cathode pad dimensions 18.8mm x 14.4mm. Anode pad dimensions 5.6mm x 14.4mm

Typical Characteristics

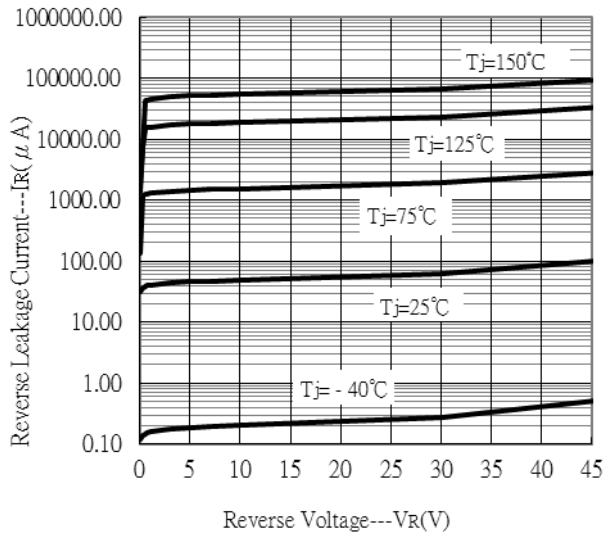
Forward Current Derating Curve



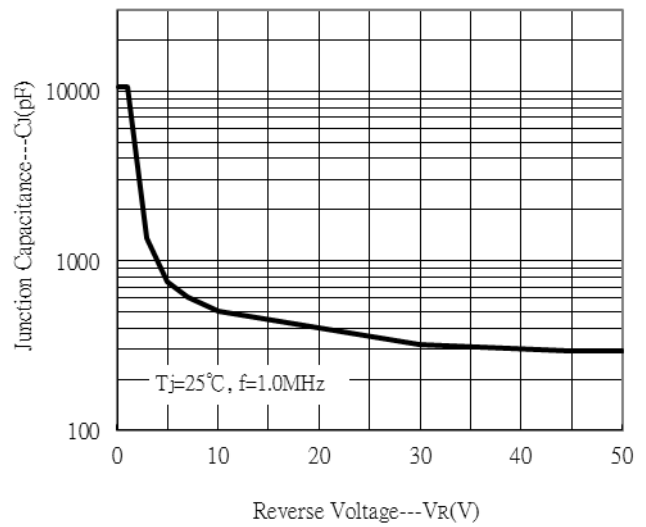
Forward Current vs Forward Voltage



Reverse Leakage Current vs Reverse Voltage

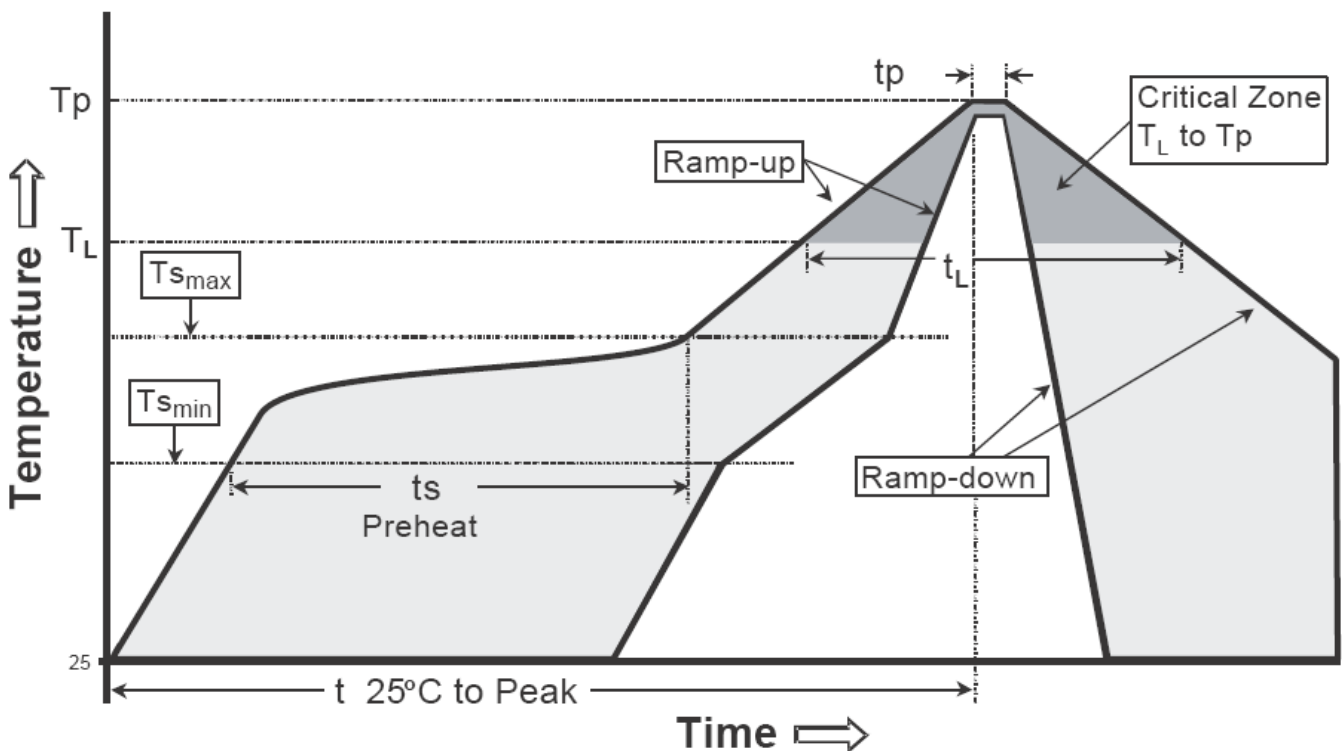


Junction Capacitance vs Reverse Voltage



Recommended wave soldering condition

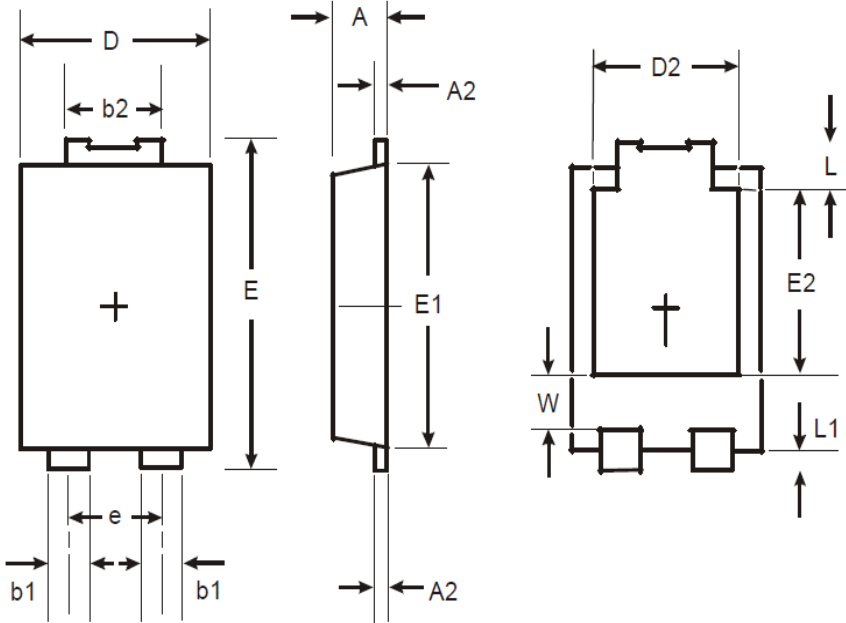
Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

Recommended temperature profile for IR reflow


Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(Ts min)	100°C	150°C
-Temperature Max(Ts max)	150°C	200°C
-Time(ts min to ts max)	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (TL)	183°C	217°C
- Time (tL)	60-150 seconds	60-150 seconds
Peak Temperature(TP)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

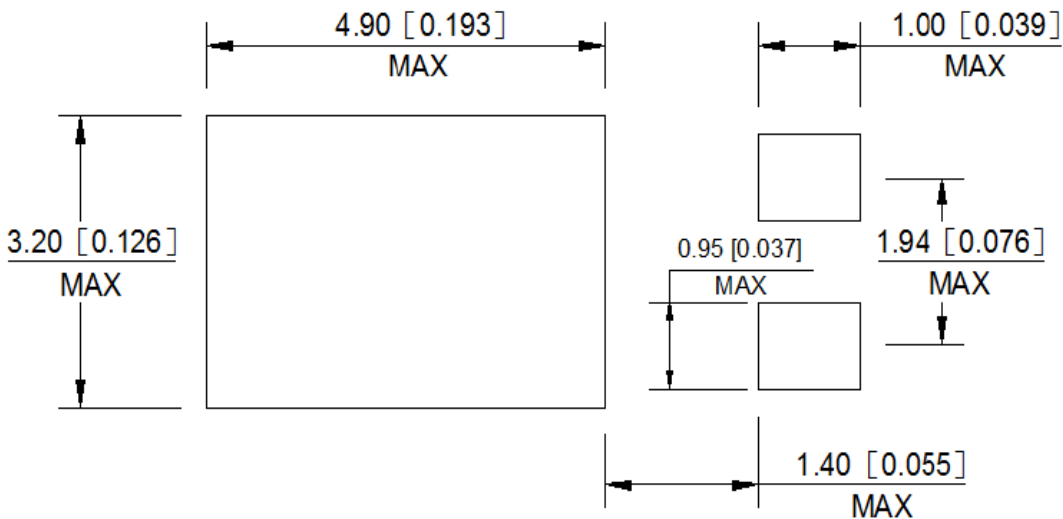
Note : All temperatures refer to topside of the package, measured on the package body surface.

TO-277 Dimension

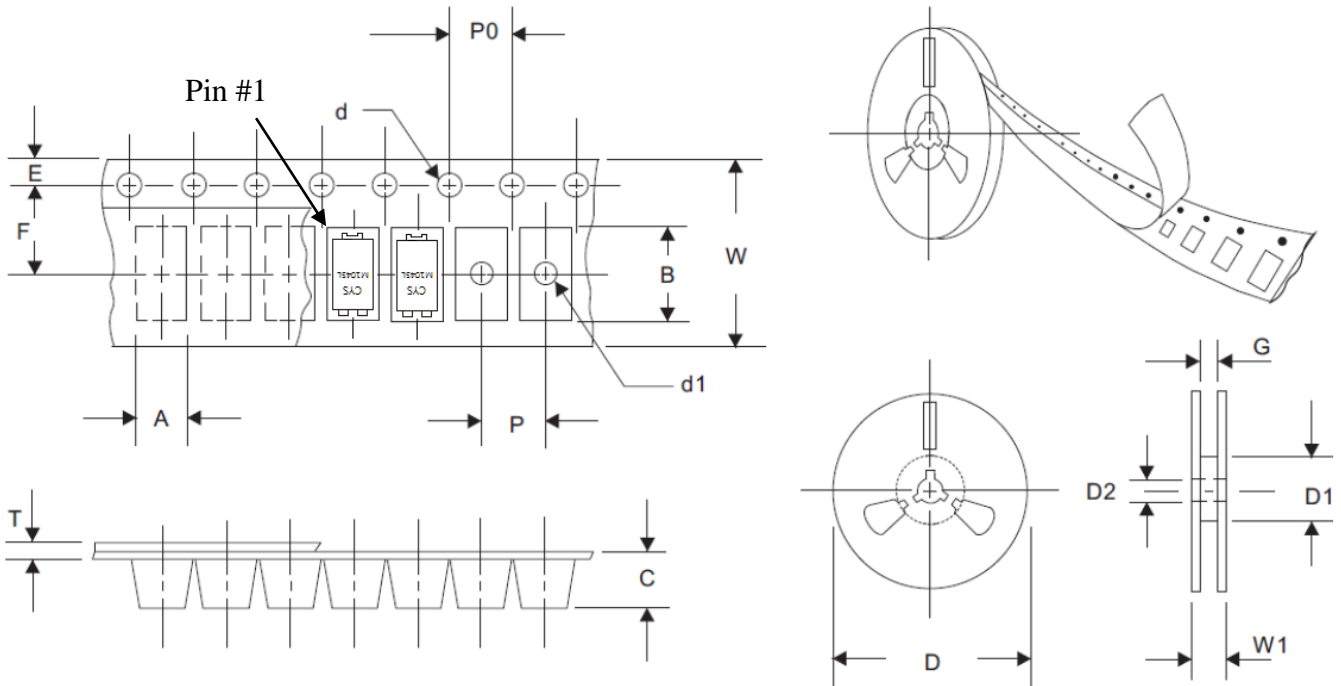


TO277		
Dim	Min	Max
A	0.95	1.25
A2	0.2	0.3
b1	0.85	0.95
b2	1.7	1.9
D	3.88	4.08
D2	2.9	3.2
E	6.3	6.7
e	1.74	1.94
E1	5.28	5.48
E2	3.4	3.7
L	0.7	1
L1	0.5	0.75
W	1.1	1.4
All Dimensions in mm		

Mounting Pad Layout



Packing Information



W	A	B	C	d1	d	E	F	P	P0	T	D	D1	D2	G	W1
12	4.38	6.9	1.4	1.5	1.5	1.75	5.5	8	4	0.34	330	72	13	12.4	18

Unit : mm

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